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Tunable dielectric properties of BaZr_{0.2}Ti_{0.8}O₃–Mg₂SiO₄–MgO composite ceramics

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1. Introduction

Electric field tunable ferroelectric materials have attracted extensive attention in recent years due to their potential applications for tunable microwave device such as tunable filters, phased array antennas, delay lines and phase shifters. These applications require a material that demonstrates high tunability, low dielectric loss, and suitable permittivity. High dielectric constant ferroelectric materials tend to have higher loss tangents and, therefore, higher insertion loss. Furthermore, a high dielectric constant can cause substantial impedance mismatch issues. Of all the ferroelectric materials investigated for tunable microwave applications, (Ba, Sr)TiO₃ solid solution has received the most attention [1–8] due to its intrinsic high dielectric tunability. Some dielectric materials with relatively low dielectric constant and loss tangent were added into (Ba, Sr)TiO₃ to reduce the effective dielectric constant and loss tangent of the (Ba, Sr)TiO₃ while maintaining respectable tunability [3-8].

Recently $BaZr_xTi_{1-x}O_3$ solid solution has shown great potential for the application in tunable microwave devices [9–15]. With increasing Zr content, phase transition peak shifts to lower temperature and the tunability and loss tangent decrease. The dielectric

ABSTRACT

 $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites were prepared by a solid-state reaction method, and their dielectric and tunable characteristics were investigated for the potential application as microwave tunable materials. It is observed that the addition of Mg_2SiO_4-MgO into $BaZr_{0.2}Ti_{0.8}O_3$ form ferroelectric ($BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$) composites. The dielectric constant and loss tangent of $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites have been reduced and the overall tunability is maintained at a sufficiently high level. An anomalous relation between dielectric constant and tunability was observed: with the increase of Mg_2SiO_4 content (>30 wt%), the dielectric constant of composite decreases and the tunability increases. The anomalous increased tunability can be attributed to redistribution of the electric field. $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites have tunability of 14.2–17.9% at 100 kHz under 2 kV/mm, indicating that it is a promising candidate material for tunable microwave applications requiring low dielectric constant.

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constant of BaZr_{0.2}Ti_{0.8}O₃ at room temperature at 1 MHz is as high as ~22,000 [12,16]. High dielectric constant has restricted its application in tunable microwave device. It is necessary to decrease the dielectric constant of BaZr_xTi_{1-x}O₃. It is reported that forming ferroelectric–dielectric composite is an efficient method to decrease dielectric constant and loss tangent while maintaining the tunability at a sufficiently high level [3,4]. Maiti et al. [12,16,17] have reported high tunability and low loss tangent of the Ba(Zr_xTi_{1-x})O₃:MgO composites which show the dielectric constant <400 in the temperature range from 300 K to 11 K. 50 wt% BaZr_{0.2}Ti_{0.8}O₃-50 wt% MgO has a tunability 22% under 3 kV/mm biasing versus a dielectric constant 219 (10 kHz) and the sintering temperature is as high as 1500 °C.

In this paper, MgO and Mg₂SiO₄ have been introduced to fabricate the BaZr_{0.2}Ti_{0.8}O₃–Mg₂SiO₄–MgO composites for tunable microwave devices applications. MgO and Mg₂SiO₄ are microwave dielectric materials with low dielectric constant and loss tangent, and their combination tailored the dielectric properties of BaZr_{0.2}Ti_{0.8}O₃ ceramics to make it useful in an array of different applications similar to the (Ba, Sr)TiO₃:MgO [3,4], furthermore, the sintering temperature can be reduced. 40BaZr_{0.2}Ti_{0.8}O₃–(60 – *x*)Mg₂SiO₄–*x*MgO (where *x* = 48, 36, 30, 24 and 12 wt%) composite ceramics have been prepared and their microstructure and dielectric tunable characteristics have been studied for the potential application as microwave tunable materials.

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Fig. 1. The XRD patterns of $40BaZr_{0.2}Ti_{0.8}O_3 - (60 - x)Mg_2SiO_4 - xMgO$ composite ceramics sintered at $1350 \degree C$ for 3 h. (a) x = 48 wt%, (b) x = 36 wt%, (c) x = 30 wt%, (d) x = 24 wt%, and (e) x = 12 wt%.

2. Experimental procedures

2.1. Synthesis of composite ceramics

Ceramic samples were prepared by the conventional solid-state route. BaZr_{0.2}Ti_{0.8}O₃ and Mg₂SiO₄ powders were prepared first from BaCO₃, ZrO₂, TiO₂ and MgO, SiO₂ powders at 1200 °C, respectively. The BaZr_{0.2}Ti_{0.8}O₃ powders were mixed with Mg₂SiO₄ and MgO according to the formalism 40BaZr_{0.2}Ti_{0.8}O₃–(60 – x)Mg₂SiO₄–xMgO (where x = 48, 36, 30, 24 and 12 wt%) and milled with agate balls for 6 h. After adding the binder the composite powders were pressed into pellets and subsequently sintered at temperatures 1300–1350 °C for 3 h. Silver paste was coated to form electrodes on both sides of the sintered ceramic samples for dielectric measurements.

2.2. Characterization

The crystal phases of the sintered samples were determined by powder X-ray diffraction (XRD) using Cu K α radiation (X'Pert PRO of PANalytical B.V.,) after crushing and grinding. The collection conditions were as follows: 40 kV, 40 mA, 2 θ range: 10–80°, step scan: 0.0167°, scan type: continuous. The Hitachi S-4800 field emission scanning electron microscopy with energy dispersive analysis system of X-ray (EDS, Horiba EMAX ENERGY EX-350) was used to characterize the microstructure and chemical component elements. The dielectric constant and loss tangent were measured using Agilent 4294A precision impedance analyzer at 100 kHz. The tunability was measured with a LCR meter at biases up to 1000 V d.c. via an external power supply.

3. Results and discussion

Fig. 1 shows the XRD patterns of $40BaZr_{0.2}Ti_{0.8}O_{3-}(60-x)Mg_2SiO_4-xMgO$ ceramics sintered at 1350 °C for 3 h. Three distinguished crystalline phases, cubic $BaZr_{0.2}Ti_{0.8}O_3$, orthorhombic Mg_2SiO_4 , and cubic MgO, were observed but no other phase was detected. With the decrease of MgO content and the increase of Mg_2SiO_4 content, the diffraction peaks from MgO decrease gradually and the diffraction peaks from Mg_2SiO_4 and MgO are distributed as individual phases in the final composite bulk ceramics.

the FFSFM Fig 2 shows images of $40\text{BaZr}_{0.2}\text{Ti}_{0.8}\text{O}_3 - (60 - x)\text{Mg}_2\text{SiO}_4 - x\text{MgO}$ composite ceramics sintered at 1350 °C for 3 h. The FESEM image and element mapping of $40BaZr_{0.2}Ti_{0.8}O_3 - (60 - x)Mg_2SiO_4 - xMgO$ (x = 48 and 24) as determined by energy dispersive spectroscopy (EDS) are shown in Fig. 3. Three kind of different grains can be found clearly: dark, nearly round larger grains, platelike grains with sharp corner and light, smaller grains with average grain size of about $0.5 \,\mu$ m. The element mapping of Si K α 1 and Ba L α 1 in Fig. 3 can show the distribution of Mg₂SiO₄ and BaZr_{0.2}Ti_{0.8}O₃ grains clearly. Therefore, we can identify that the dark, larger grains are MgO; white, smaller grains are BaZr_{0.2}Ti_{0.8}O₃; and the platelike grains are Mg₂SiO₄. With the decrease of MgO content and the increase of Mg₂SiO₄ content, more and more Mg₂SiO₄ grains can be found (Fig. 2). MgO grains become smaller with the decrease of MgO content (Fig. 3b). We can conclude that Mg₂SiO₄ and MgO were randomly dispersed relative to the ferroelectric BaZr_{0.2}Ti_{0.8}O₃ phase without any detectable new phase as shown in Fig. 2.

From the XRD and FESEM study, we know that BaZr_{0.2}Ti_{0.8}O₃-Mg₂SiO₄-MgO composite ceramics are composed of tunable ferroelectric phase BaZr_{0.2}Ti_{0.8}O₃ and dielectric phases Mg₂SiO₄ and MgO. Because of the relatively low dielectric constant and loss tangent of Mg₂SiO₄ and MgO, it is expected that BaZr_{0.2}Ti_{0.8}O₃-Mg₂SiO₄-MgO composites have lower dielectric constant and loss tangent. Fig. 4 shows the dielectric constant and loss tangent of BaZr_{0.2}Ti_{0.8}O₃-Mg₂SiO₄-MgO composite ceramics at 100 kHz. With the increase of sintering temperature from 1300 °C to 1350 °C, the dielectric constant of the composites increase and the loss tangent decrease. Increasing Mg₂SiO₄ content tends to decrease the dielectric constant of composites, which is due to lower dielectric constant of Mg₂SiO₄ than that of MgO. The dielectric constant of composites is much smaller than that of BaZr_{0.2}Ti_{0.8}O₃ ($\varepsilon \sim 22,000$ at 100 kHz) [12,16]. Low dielectric constant will improve the ability to the impedance match to the device. On the other hand, the loss tangent of composites sintered at 1350°C is ~0.0012-0.0016, which is comparable to that of 50BaZr_{0.2}Ti_{0.8}O₃-50MgO [16,17]. Adding Mg₂SiO₄ and MgO into $BaZr_{0,2}Ti_{0,8}O_3$, three phases ($BaZr_{0,2}Ti_{0,8}O_3$, Mg_2SiO_4 and MgO) composites formed and the dielectric constant and loss tangent decreased, just as we expected.

The tunability may be defined as (dielectric constant with no applied voltage)–(dielectric constant with an applied voltage)/(dielectric constant with no applied voltage). For simplicity purposes, tunability can be represented as

$$T = \frac{\varepsilon(0) - \varepsilon(E)}{\varepsilon(0)} = \frac{C(0) - C(E)}{C(0)}$$

where C is the capacitance and E is the applied dc electric field. Fig. 5 shows the effect of applied field on the tunability of the BaZr_{0.2}Ti_{0.8}O₃-Mg₂SiO₄-MgO composites at 100 kHz at room temperature. The tunability of 40BaZr_{0.2}Ti_{0.8}O₃-12Mg₂SiO₄-48MgO under 2 kV/mm is 15.6%. With the increase of Mg₂SiO₄ content, the tunability of 40BaZr_{0.2}Ti_{0.8}O₃-30Mg₂SiO₄-30MgO decreases slightly to 14.2%. Further increasing Mg₂SiO₄ content results in an anomalous increase of tunability: 40BaZr_{0.2}Ti_{0.8}O₃-48Mg₂SiO₄-12MgO composite has lower dielectric constant than 40BaZr_{0.2}Ti_{0.8}O₃-12Mg₂SiO₄-48MgO but slightly higher tunability (17.9%). Compared with binary $50BaZr_{0.2}Ti_{0.8}O_3-50MgO$, $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites have reduced dielectric constant, comparable tunability [17], but lower sintering temperature. Decreasing dielectric constant by ferroelectric-dielectric composite method is usually strongly correlated a decrease in tunability. In order to decrease dielectric constant of composite, it is necessary to increase the dielectrics content. For example [3], increasing MgO content in Ba_{0.6}Sr_{0.4}TiO₃-MgO from 30 wt% to 60 wt% results in a decrease





Fig. 2. FESEM images of $40BaZr_{0.2}Ti_{0.8}O_3 - (60 - x)Mg_2SiO_4 - xMgO$ composites ceramics sintered at 1350 °C for 3 h. From (a) to (e), x = 48 wt%, 36 wt%, 30 wt%, 24 wt% and 12 wt%, respectively.

of dielectric constant from 636 to 118 and tunability at 2 kV/mm from 15% to 10%. No literatures reported the effect of MgO content on the dielectric constant and tunability of BZT/MgO composite. We can expect the similar results with BST/MgO. Therefore, it is difficult to decrease the dielectric constant of two-phase composites and increase their tunability. In present work, an anomalous relation between dielectric constant and tunability was observed in three-phase BaZr_{0.2}Ti_{0.8}O₃-Mg₂SiO₄-MgO composites: with increasing Mg₂SiO₄ content above 30 wt%, the dielectric constant

of composite decreases and the tunability increases. It is beneficial to tunable application.

As Tagantsev stated [18], mixing a tunable ferroelectric with a linear dielectric may modify the electrical properties of the material due to mainly two effects: (i) "doping effect" – effect of doping of the ferroelectric lattice via the substitution of the ions of the host material and (ii) "composite effect" – effects of redistribution of the electric field in the material due to the precipitation of the non-ferroelectric phase at the grain boundaries or in the bulk of





Si Kal

Ba Lα1



Fig. 3. FESEM image and element mapping of $40BaZr_{0.2}Ti_{0.8}O_3 - (60 - x)Mg_2SiO_4 - xMgO$ as determined by energy dispersive spectroscopy (EDS). (a) x = 48 wt% and (b) x = 24 wt%.



Fig. 4. Dielectric constant (solid) and loss tangent (open) of $40BaZr_{0.2}Ti_{0.8}O_3-(60-x)Mg_2SiO_4-xMgO$ composite ceramics sintered at various temperatures.

the material. For $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composite, the first effect can be ignored. The big contrast in the values of dielectric constants of linear dielectrics (Mg_2SiO_4-MgO) and the ferroelectric ($BaZr_{0.2}Ti_{0.8}O_3$) affects the redistribution of the electric field around the dielectrics. The dielectric constant of the ferroelectric under applied electric field becomes in-homogeneously distributed over the volume of the ferroelectric. The overall tunability of the composite, thus changes. Two competitive phenomena affect the tunable properties of the ferroelectric when it is diluted with a dielectric [19]. First, the reduction of the volume of ferroelectric, which is responsible for tuning, will cause suppression of the tunability of the material. Second, the redistribution of the electric field surrounding the linear dielectrics will affect the local tuning of the ferroelectric. Depending on the shape of the linear



Fig. 5. The tunability of $40BaZr_{0.2}Ti_{0.8}O_3-(60-x)Mg_2SiO_4-xMgO$ composites at 100 kHz at room temperature (sintering temperature: 1350 °C).

dielectrics and on the dielectric constants of the components, the impact of each of these two effects on the composite tunability is different and the second effect may be stronger [19]. With the increase of Mg₂SiO₄ content and the decrease of MgO content, the volume of ferroelectric $BaZr_{0.2}Ti_{0.8}O_3$ decrease due to smaller density of Mg₂SiO₄ than that of MgO, the tunability of composite will be suppressed. It is the fact as x decreases from 48 wt% to 30 wt%. The anomalous increased tunability in composite with x < 30 wt% can be attributed to redistribution of the electric field. Mg₂SiO₄ and MgO have different dielectric constants, they will have different effects on the redistribution of the electric field. The combination of linear dielectrics with different dielectric constants can result in the change of dielectric constant and loss tangent and even increase the tunability by affecting the redistribution of the electric field in the composite. As x decreases from 30 wt% to 12 wt%, the increase of the tunability due to redistribution of the electric field exceeds the decrease of the tunability due to ferroelectric dilution, so the tunability of composite ceramics increases anomalously.

4. Conclusions

 $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites were prepared by conventional solid-state route and their microstructure and dielectric properties were investigated for tunable microwave applications. XRD patterns showed that ferroelectric ($BaZr_{0.2}Ti_{0.8}O_3$) and dielectric (Mg_2SiO_4-MgO) three phase composites were formed. The $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites exhibited relatively high tunability in combination with reduced dielectric permittivity and low loss tangent. An anomalous relation between dielectric constant and tunability was observed. The tunability of $BaZr_{0.2}Ti_{0.8}O_3-Mg_2SiO_4-MgO$ composites was 14.2–17.9% at 100 kHz under 2 kV/mm, indicating that it is a promising candidate material for tunable microwave applications requiring low dielectric constant.

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